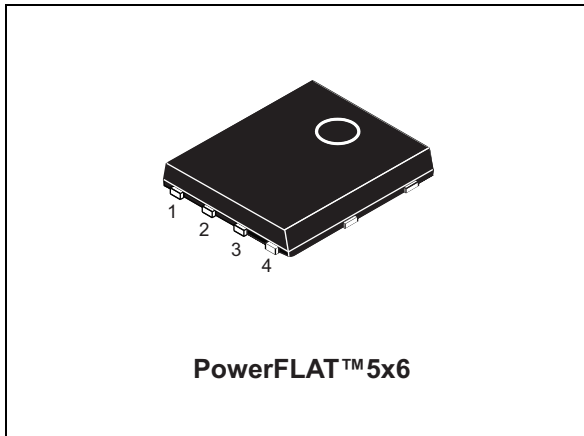
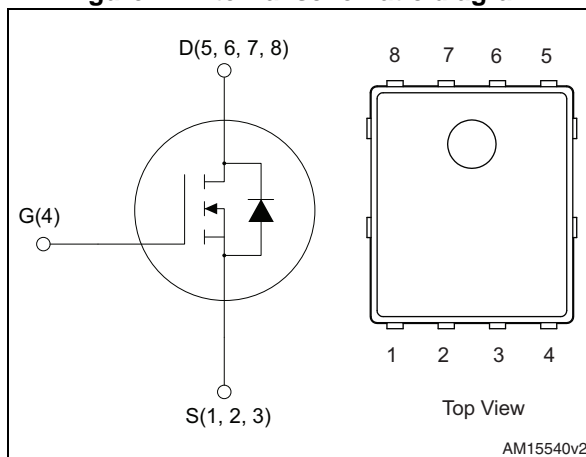


## N-channel 30 V, 0.0014 $\Omega$ typ., 35 A STripFET™ V Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data



**Figure 1. Internal schematic diagram**



### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$
STL150N3LLH5	30 V	0.00175 $\Omega$	35 A <sup>(1)</sup>

1. The value is rated according  $R_{thj-pcb}$

- $R_{DS(on)} * Q_g$  industry benchmark
- Extremely low on-resistance  $R_{DS(on)}$
- High avalanche ruggedness
- Low gate drive power losses

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to a FOM that is among the best in its class.

**Table 1. Device summary**

Order code	Marking	Packages	Packaging
STL150N3LLH5	150N3LH5	PowerFLAT™ 5X6	Tape and reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	30	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	195	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	122	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	35	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	21.8	A
$I_{DM}^{(3)}$	Drain current (pulsed)	140	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	114	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4	W
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. The value is rated according  $R_{thj-c}$
2. The value is rated according  $R_{thj-pcb}$
3. Pulse width limited by safe operating area

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.1	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AV}$	Not-repetitive avalanche current, (pulse width limited by $T_{j,max}$ )	17	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AV}$ , $V_{DD} = 24\text{ V}$ )	300	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 30\text{ V}$ $V_{GS} = 0$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}$ , $V_{GS} = 0$ $T_C = 125\text{ °C}$			10	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{GS} = \pm 22\text{ V}$ , $V_{DS} = 0$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1	1.55	2.2	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 17.5\text{ A}$		0.0014	0.00175	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 17.5\text{ A}$		0.0019	0.0024	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	5800	-	pF
$C_{oss}$	Output capacitance		-	1147	-	pF
$C_{rss}$	Reverse transfer capacitance		-	127	-	pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}$ , $I_D = 35\text{ A}$ $V_{GS} = 4.5\text{ V}$ (see Figure 14)	-	40	-	nC
$Q_{gs}$	Gate-source charge		-	13.4	-	nC
$Q_{gd}$	Gate-drain charge		-	14.9	-	nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ , gate DC Bias = 0, test signal level = 20 mV, $I_D = 0$	-	1.1	-	$\Omega$

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$ , $I_D=17.5\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=10\text{ V}$ (see Figure 13)	-	17.2	-	ns
$t_r$	Rise time		-	30.8	-	ns
$t_{d(off)}$	Turn-off delay time		-	65.8	-	ns
$t_f$	Fall time		-	47.8	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		35	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		140	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 35\text{ A}$ , $V_{GS}=0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 35\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 25\text{ V}$	-	43.8		ns
$Q_{rr}$	Reverse recovery charge		-	46		nC
$I_{RRM}$	Reverse recovery current		-	2.1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

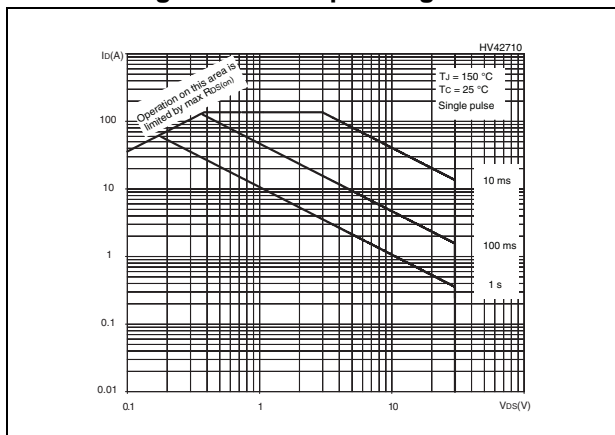


Figure 3. Thermal impedance

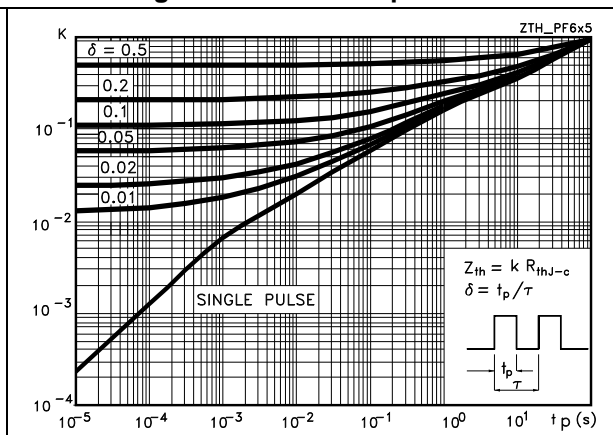


Figure 4. Output characteristics

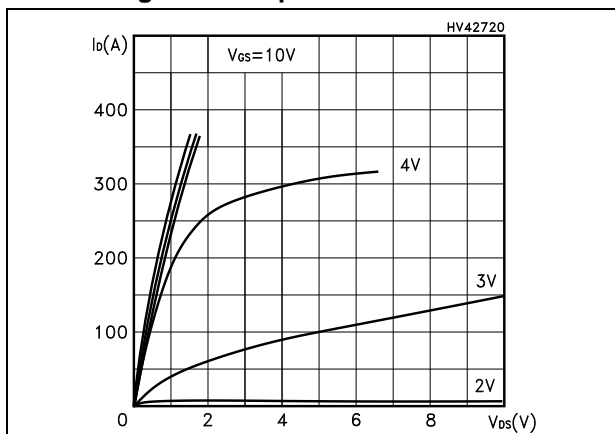


Figure 5. Transfer characteristics

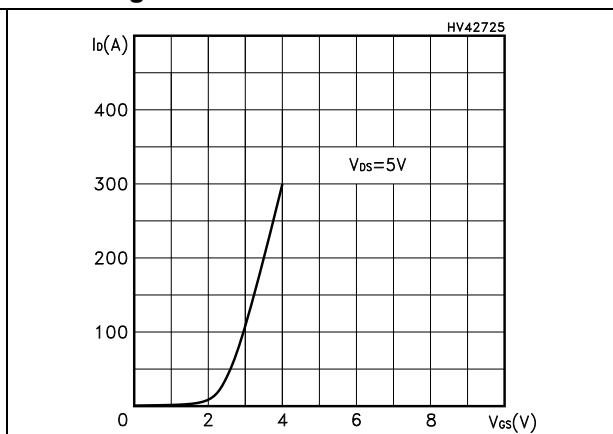


Figure 6. Normalized BV<sub>DSS</sub> vs temperature

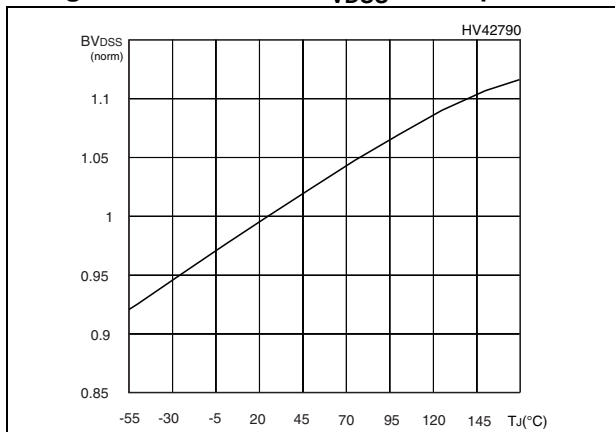


Figure 7. Static drain-source on-resistance

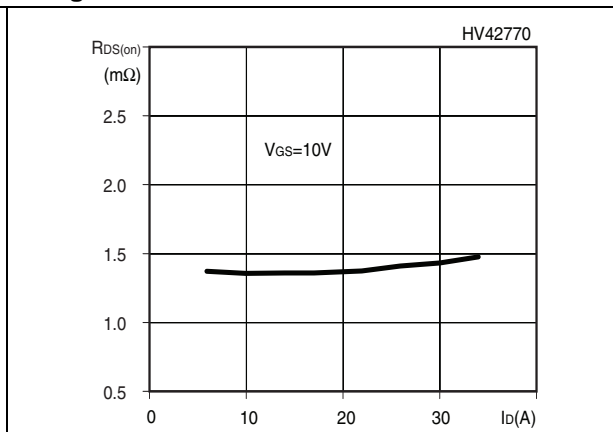


Figure 8. Gate charge vs gate-source voltage

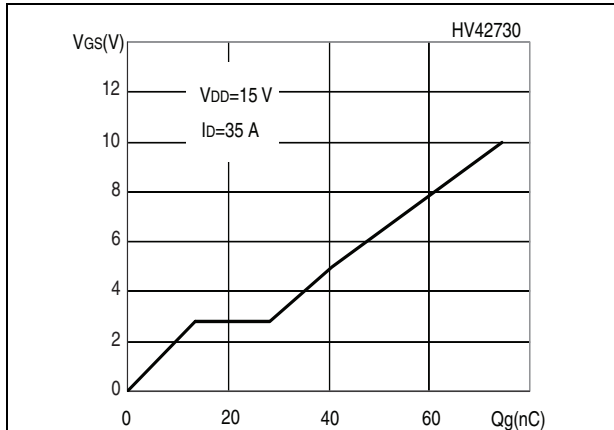


Figure 9. Capacitance variations

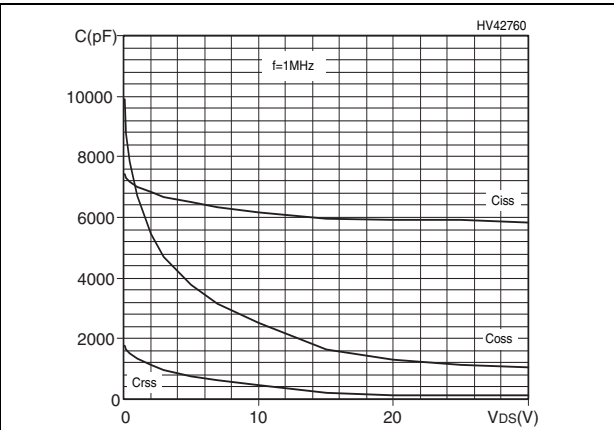


Figure 10. Normalized gate threshold voltage vs temperature

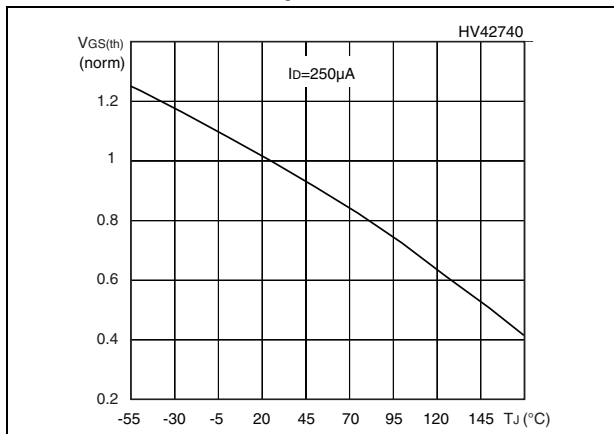


Figure 11. Normalized on-resistance vs temperature

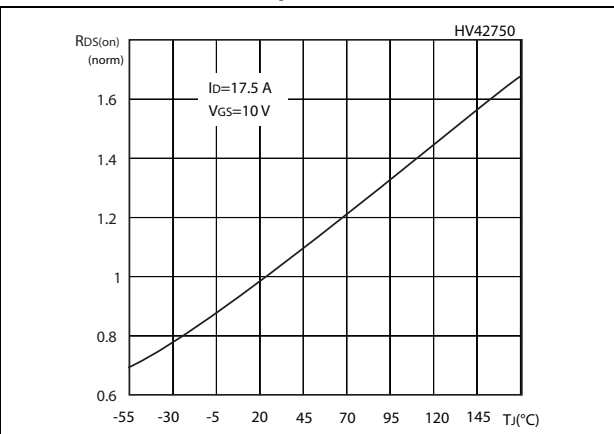
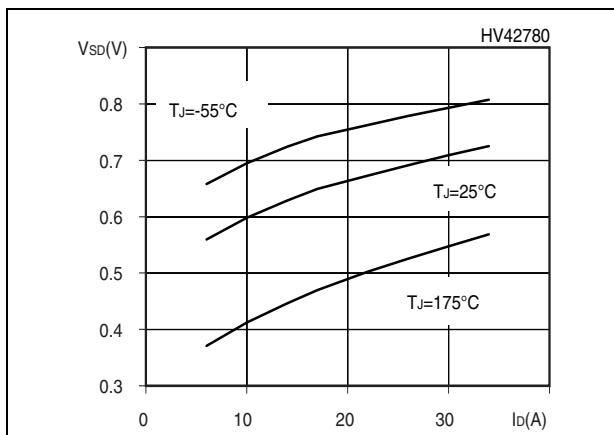


Figure 12. Source-drain diode forward characteristics



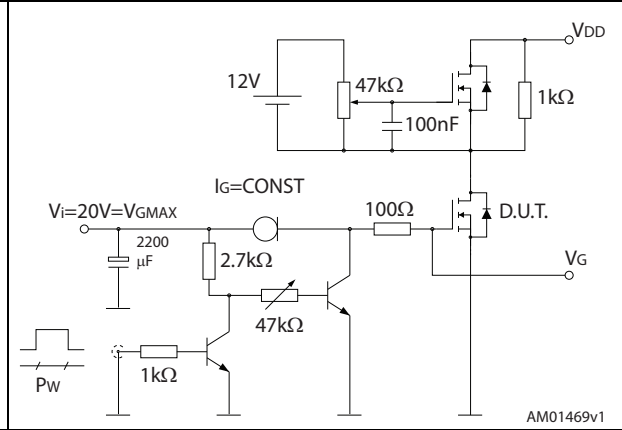
### 3 Test circuits

Figure 13. Switching times test circuit for resistive load



AM01468v1

Figure 14. Gate charge test circuit



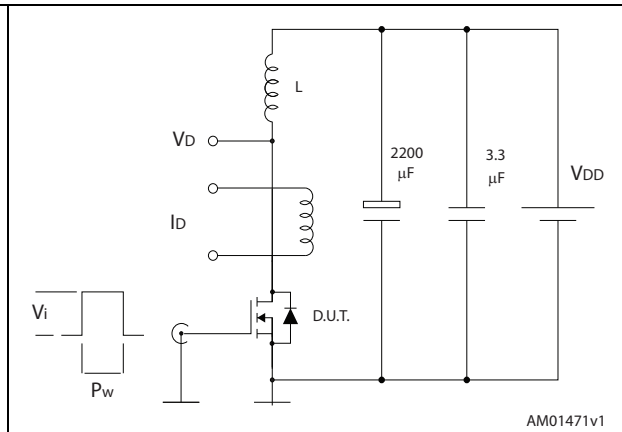
AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



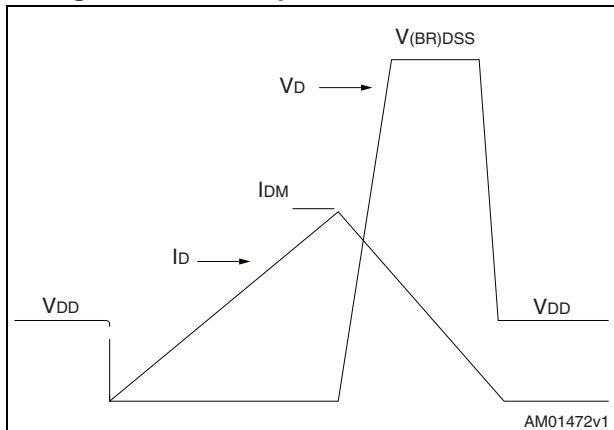
AM01470v1

Figure 16. Unclamped inductive load test circuit



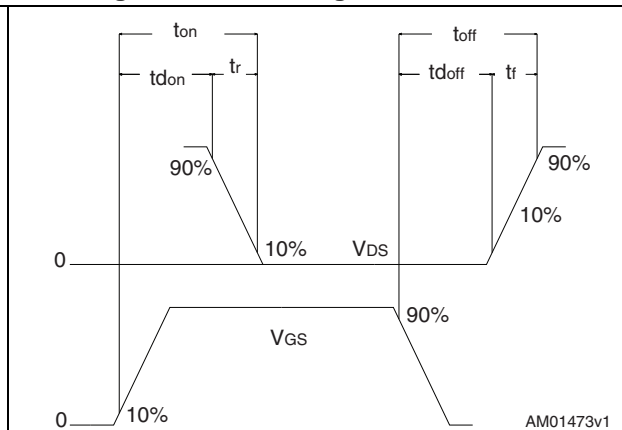
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 19. PowerFLAT™ 5x6 type S-C mechanical data

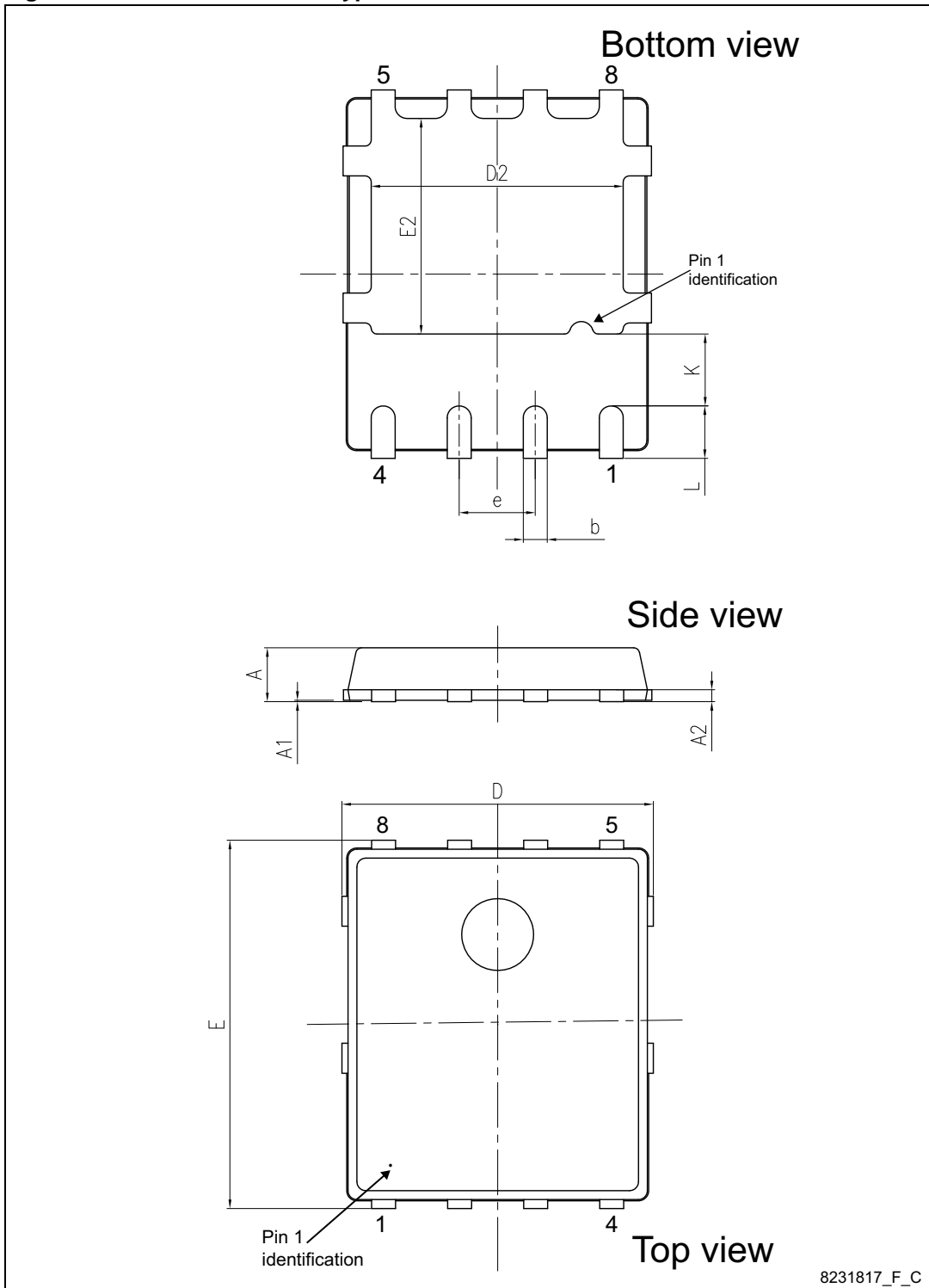
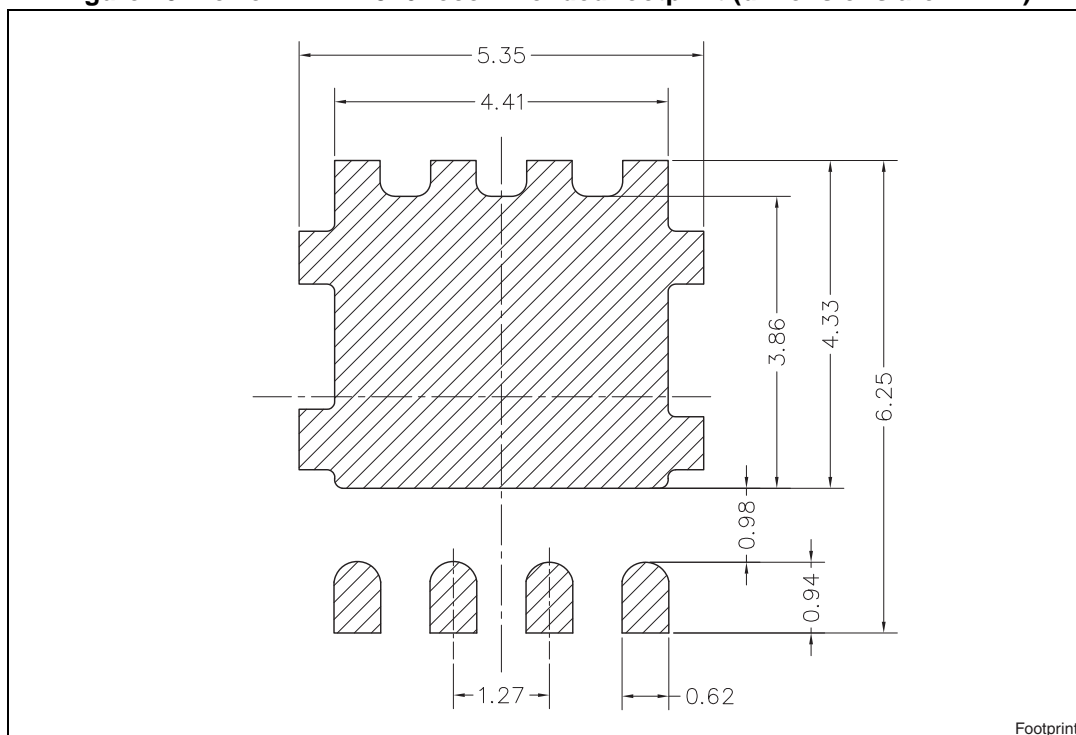


Figure 20. PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



## 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
22-Oct-2007	1	First release
01-Apr-2008	2	Document status promoted from preliminary data to datasheet
23-Sep-2008	3	$V_{GS}$ value has been changed on <a href="#">Table 2</a> and <a href="#">Table 5</a>
12-Jun-2009	4	$V_{GS(th)}$ value has been changed on <a href="#">Table 5</a>
05-Oct-2011	5	<a href="#">Section 4: Package mechanical data</a> has been updated. Minor text changes.
30-Aug-2013	6	<ul style="list-style-type: none"><li>– Modified: <a href="#">Figure 1</a> and marking in <a href="#">Table 1</a></li><li>– Modified: <math>I_D</math> value in <a href="#">Figure 11</a></li><li>– Updated: <a href="#">Figure 13</a>, <a href="#">14</a>, <a href="#">15</a> and <a href="#">16</a></li><li>– Updated: <a href="#">Section 4: Package mechanical data</a></li></ul>

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